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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, SPI, UART/USART
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	57
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 39x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	121-LFBGA
Supplier Device Package	121-MAPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk10dx64vmb7

3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

3.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

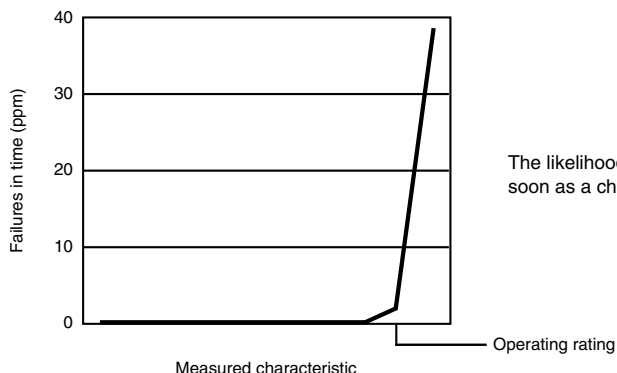
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

3.4.1 Example

This is an example of an operating rating:

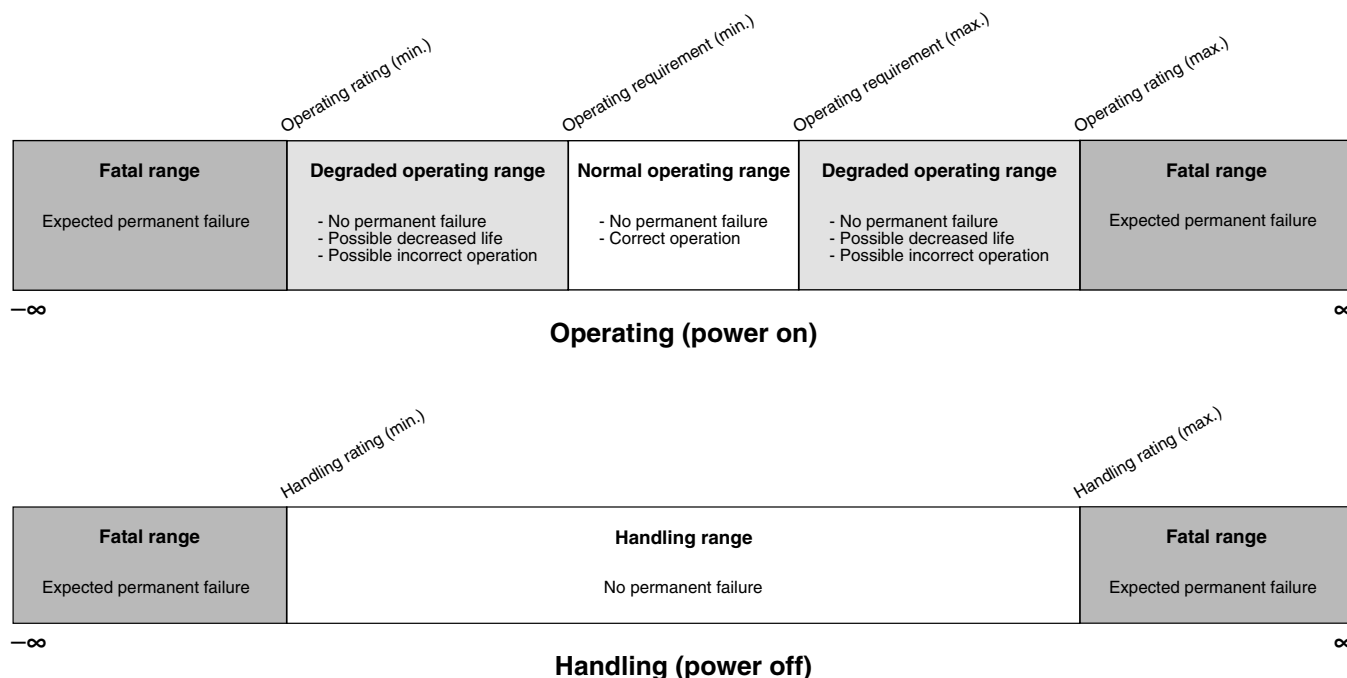
Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	−0.3	1.2	V

3.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

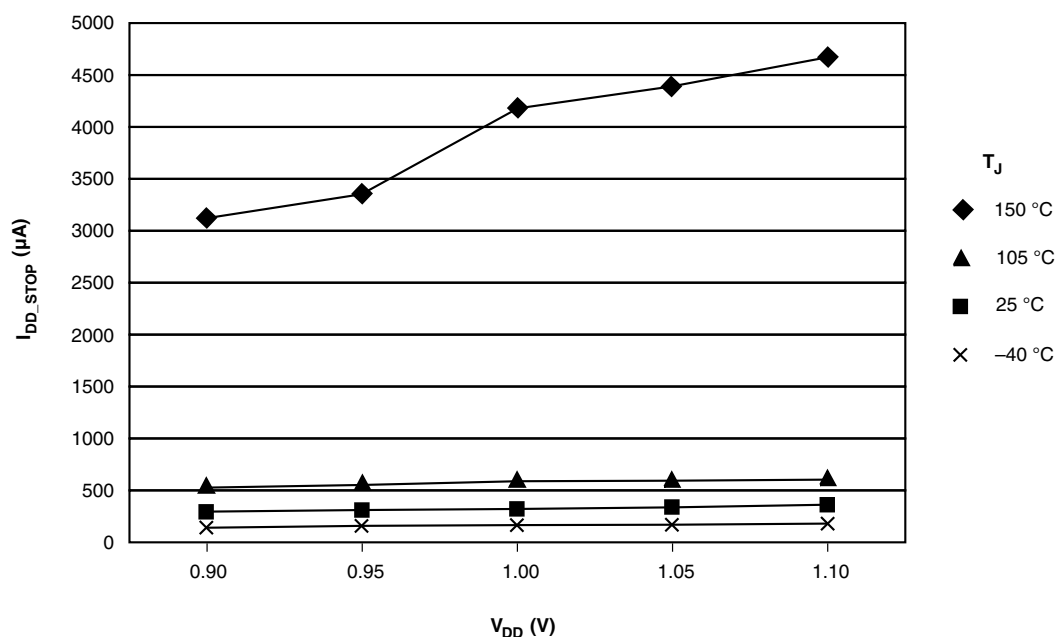
3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	μA

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



3.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	3.3 V supply voltage	3.3	V

5.2.3 Voltage and current operating behaviors

Table 4. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — high drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OH} = -9\text{mA}$	$V_{DD} - 0.5$	—	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OH} = -3\text{mA}$	$V_{DD} - 0.5$	—	V	
	Output high voltage — low drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OH} = -2\text{mA}$	$V_{DD} - 0.5$	—	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OH} = -0.6\text{mA}$	$V_{DD} - 0.5$	—	V	
I_{OHT}	Output high current total for all ports	—	100	mA	
V_{OL}	Output low voltage — high drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OL} = 9\text{mA}$	—	0.5	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OL} = 3\text{mA}$	—	0.5	V	
	Output low voltage — low drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OL} = 2\text{mA}$	—	0.5	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OL} = 0.6\text{mA}$	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	100	mA	
I_{IN}	Input leakage current (per pin) for full temperature range	—	1	μA	1
I_{IN}	Input leakage current (per pin) at 25°C	—	0.025	μA	1
I_{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	
R_{PU}	Internal pullup resistors	20	50	k Ω	2
R_{PD}	Internal pulldown resistors	20	50	k Ω	3

1. Measured at $V_{DD}=3.6\text{V}$

2. Measured at V_{DD} supply voltage = V_{DD} min and $V_{input} = V_{SS}$

3. Measured at V_{DD} supply voltage = V_{DD} min and $V_{input} = V_{DD}$

5.2.4 Power mode transition operating behaviors

All specifications except t_{POR} , and $V_{LLSx} \rightarrow \text{RUN}$ recovery times in the following table assume this clock configuration:

- CPU and system clocks = 72 MHz
- Bus clock = 36 MHz
- FlexBus clock = 36 MHz
- Flash clock = 24 MHz

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip.	—	300	μs	1
	• VLLS1 → RUN	—	112	μs	
	• VLLS2 → RUN	—	74	μs	
	• VLLS3 → RUN	—	73	μs	
	• LLS → RUN	—	5.9	μs	
	• VLPS → RUN	—	5.8	μs	
	• STOP → RUN	—	4.2	μs	

1. Normal boot (FTFL_OPT[LPBOOT]=1)

5.2.5 Power consumption operating behaviors

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash	—	21.5	25	mA	2
		—	21.5	30	mA	
I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash	—	31	34	mA	3, 4
		—	31	34	mA	
		—	32	39	mA	
		—	32	39	mA	
I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	12.5	—	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	7.2	—	mA	5
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	0.996	—	mA	6

Table continues on the next page...

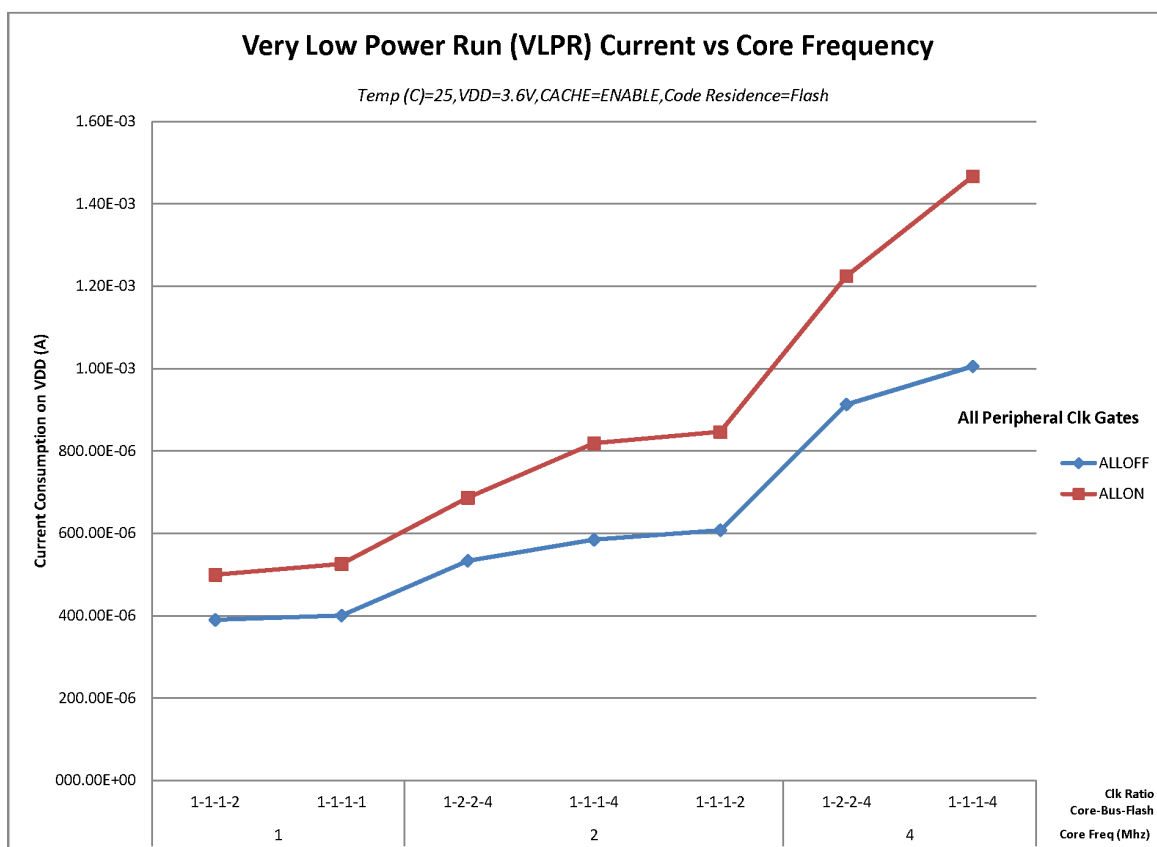


Figure 3. VLPR mode supply current vs. core frequency

5.2.6 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to <http://www.freescale.com>.
2. Perform a keyword search for “EMC design.”

5.2.7 Capacitance attributes

Table 7. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C _{IN_A}	Input capacitance: analog pins	—	7	pF

Table continues on the next page...

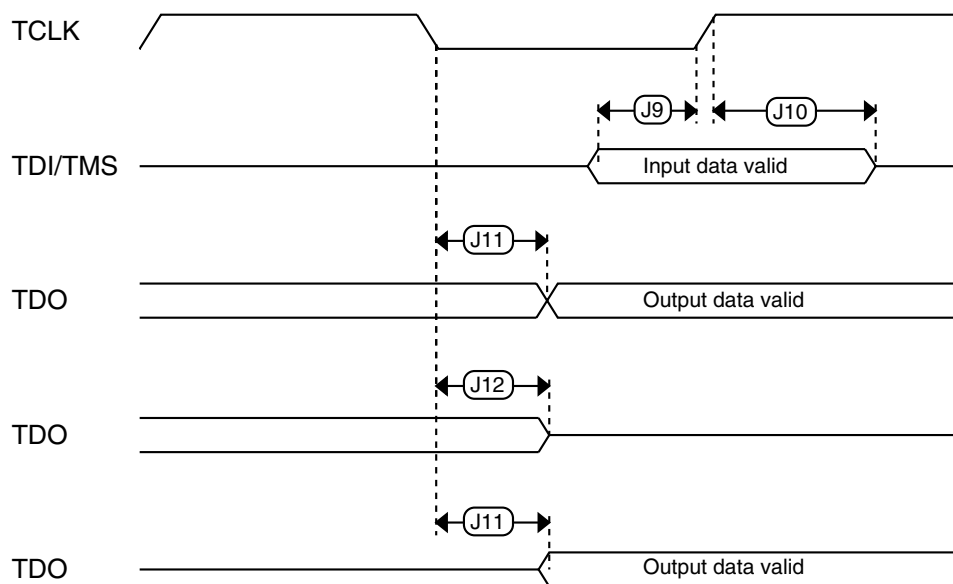


Figure 8. Test Access Port timing

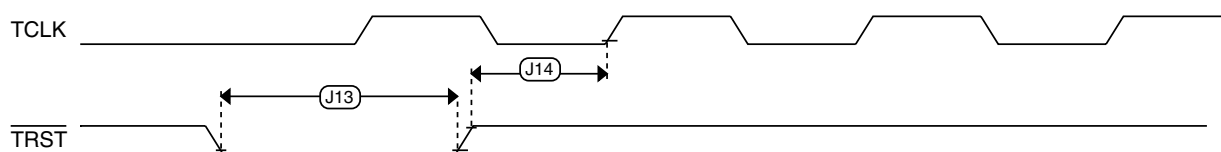


Figure 9. $\overline{\text{TRST}}$ timing

6.2 System modules

There are no specifications necessary for the device's system modules.

6.3 Clock modules

Table 19. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t _{pgmchk}	Program Check execution time	—	—	45	μs	1
t _{rdsrc}	Read Resource execution time	—	—	30	μs	1
t _{pgm4}	Program Longword execution time	—	65	145	μs	
t _{ersblk32k}	Erase Flash Block execution time <ul style="list-style-type: none">32 KB data flash	—	55	465	ms	2
t _{ersblk256k}	<ul style="list-style-type: none">256 KB program flash	—	122	985	ms	
t _{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t _{pgmsec512p}	Program Section execution time <ul style="list-style-type: none">512 B program flash	—	2.4	—	ms	
t _{pgmsec512d}	<ul style="list-style-type: none">512 B data flash	—	4.7	—	ms	
t _{pgmsec1kp}	<ul style="list-style-type: none">1 KB program flash	—	4.7	—	ms	
t _{pgmsec1kd}	<ul style="list-style-type: none">1 KB data flash	—	9.3	—	ms	
t _{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	
t _{rdonce}	Read Once execution time	—	—	25	μs	1
t _{pgmonce}	Program Once execution time	—	65	—	μs	
t _{ersall}	Erase All Blocks execution time	—	175	1500	ms	2
t _{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1
t _{swapx01}	Swap Control execution time <ul style="list-style-type: none">control code 0x01	—	200	—	μs	
t _{swapx02}	<ul style="list-style-type: none">control code 0x02	—	70	150	μs	
t _{swapx04}	<ul style="list-style-type: none">control code 0x04	—	70	150	μs	
t _{swapx08}	<ul style="list-style-type: none">control code 0x08	—	—	30	μs	
t _{pgmpart32k}	Program Partition for EEPROM execution time <ul style="list-style-type: none">32 KB FlexNVM	—	70	—	ms	
t _{setramff}	Set FlexRAM Function execution time: <ul style="list-style-type: none">Control Code 0xFF	—	50	—	μs	
t _{setram8k}	<ul style="list-style-type: none">8 KB EEPROM backup	—	0.3	0.5	ms	
t _{setram32k}	<ul style="list-style-type: none">32 KB EEPROM backup	—	0.7	1.0	ms	
Byte-write to FlexRAM for EEPROM operation						
t _{eewr8bers}	Byte-write to erased FlexRAM location execution time	—	175	260	μs	3

Table continues on the next page...

Table 19. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{eewr8b8k}	Byte-write to FlexRAM execution time: • 8 KB EEPROM backup	—	340	1700	μs	
$t_{\text{eewr8b16k}}$	• 16 KB EEPROM backup	—	385	1800	μs	
$t_{\text{eewr8b32k}}$	• 32 KB EEPROM backup	—	475	2000	μs	
Word-write to FlexRAM for EEPROM operation						
$t_{\text{eewr16bers}}$	Word-write to erased FlexRAM location execution time	—	175	260	μs	
$t_{\text{eewr16b8k}}$	Word-write to FlexRAM execution time: • 8 KB EEPROM backup	—	340	1700	μs	
$t_{\text{eewr16b16k}}$	• 16 KB EEPROM backup	—	385	1800	μs	
$t_{\text{eewr16b32k}}$	• 32 KB EEPROM backup	—	475	2000	μs	
Longword-write to FlexRAM for EEPROM operation						
$t_{\text{eewr32bers}}$	Longword-write to erased FlexRAM location execution time	—	360	540	μs	
$t_{\text{eewr32b8k}}$	Longword-write to FlexRAM execution time: • 8 KB EEPROM backup	—	545	1950	μs	
$t_{\text{eewr32b16k}}$	• 16 KB EEPROM backup	—	630	2050	μs	
$t_{\text{eewr32b32k}}$	• 32 KB EEPROM backup	—	810	2250	μs	

1. Assumes 25MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

6.4.1.3 Flash current and power specifications

Table 20. Flash current and power specifications

Symbol	Description	Typ.	Unit
$I_{\text{DD_PGM}}$	Worst case programming current in program flash	10	mA

6.4.1.4 Reliability specifications

Table 21. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
Program Flash						
$t_{\text{nv mretp10k}}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{\text{nv mretp1k}}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{\text{nv mcycp}}$	Cycling endurance	10 K	50 K	—	cycles	2

Table continues on the next page...

6.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in [Table 25](#) and [Table 26](#) are achievable on the differential pins ADCx_DP0, ADCx_DM0.

The ADCx_DP2 and ADCx_DM2 ADC inputs are connected to the PGA outputs and are not direct device pins. Accuracy specifications for these pins are defined in [Table 27](#) and [Table 28](#).

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

6.6.1.1 16-bit ADC operating conditions

Table 25. 16-bit ADC operating conditions

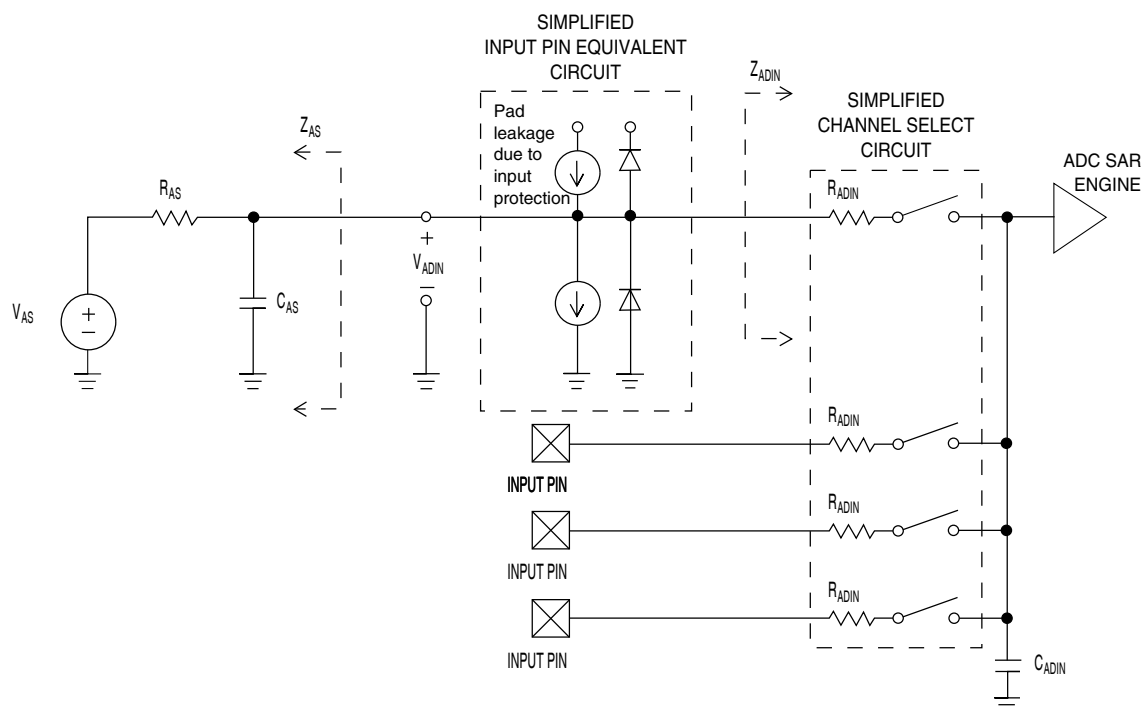
Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
V _{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV _{DDA}	Supply voltage	Delta to V _{DD} (V _{DD} -V _{DDA})	-100	0	+100	mV	2
ΔV _{SSA}	Ground voltage	Delta to V _{SS} (V _{SS} -V _{SSA})	-100	0	+100	mV	2
V _{REFH}	ADC reference voltage high		1.13	V _{DDA}	V _{DDA}	V	
V _{REFL}	Reference voltage low		V _{SSA}	V _{SSA}	V _{SSA}	V	
V _{ADIN}	Input voltage		V _{REFL}	—	V _{REFH}	V	
C _{ADIN}	Input capacitance	<ul style="list-style-type: none"> 16 bit modes 8/10/12 bit modes 	— —	8 4	10 5	pF	
R _{ADIN}	Input resistance		—	2	5	kΩ	
R _{AS}	Analog source resistance	13/12 bit modes f _{ADCK} < 4MHz	—	—	5	kΩ	3
f _{ADCK}	ADC conversion clock frequency	≤ 13 bit modes	1.0	—	18.0	MHz	4
f _{ADCK}	ADC conversion clock frequency	16 bit modes	2.0	—	12.0	MHz	4

Table continues on the next page...

Table 25. 16-bit ADC operating conditions (continued)

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
C_{rate}	ADC conversion rate	≤ 13 bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	5
C_{rate}	ADC conversion rate	16 bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	Ksps	5

1. Typical values assume $V_{DDA} = 3.0$ V, Temp = 25°C, $f_{ADCK} = 1.0$ MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. The analog source resistance should be kept as low as possible in order to achieve the best results. The results in this datasheet were derived from a system which has $<8\ \Omega$ analog source resistance. The R_{AS}/C_{AS} time constant should be kept to <1 ns.
4. To use the maximum ADC conversion clock frequency, the ADHSC bit should be set and the ADLPC bit should be clear.
5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool: http://cache.freescale.com/files/soft_dev_tools/software/app_software/converters/ADC_CALCULATOR_CNV.zip?fp=1

**Figure 14. ADC input impedance equivalency diagram**

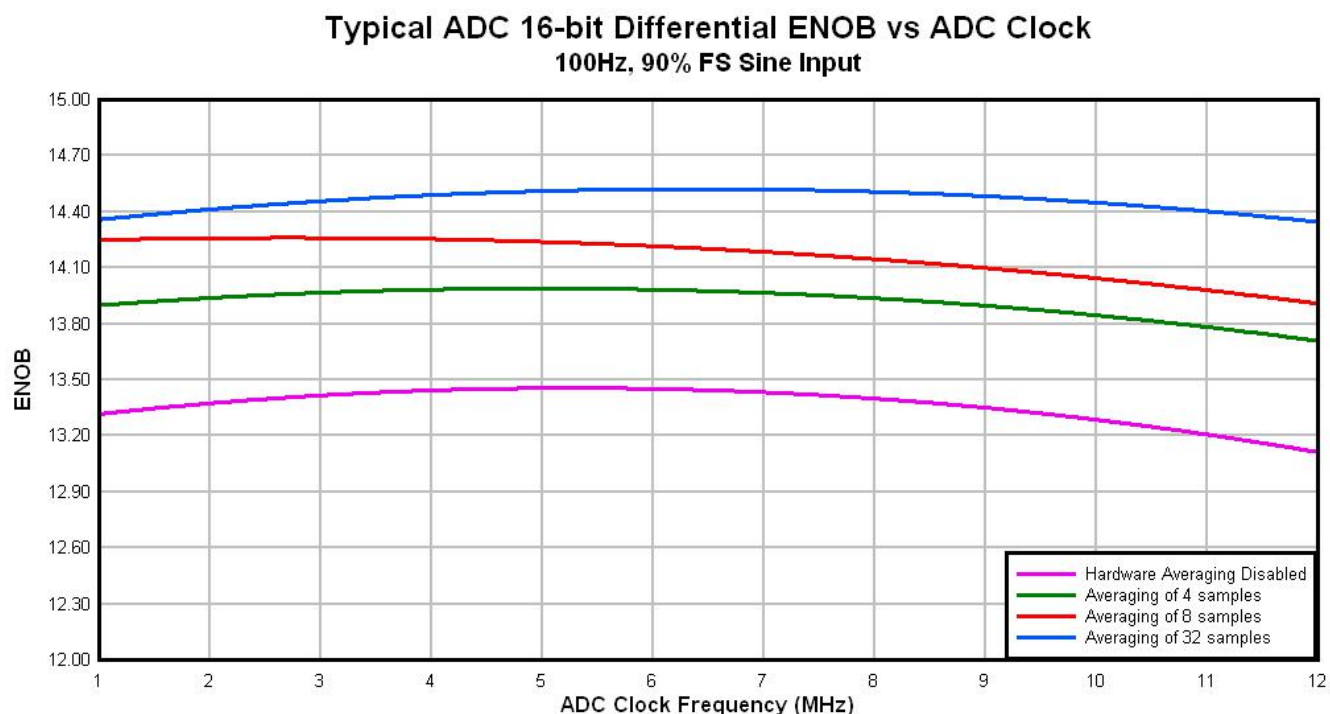


Figure 15. Typical ENOB vs. ADC_CLK for 16-bit differential mode

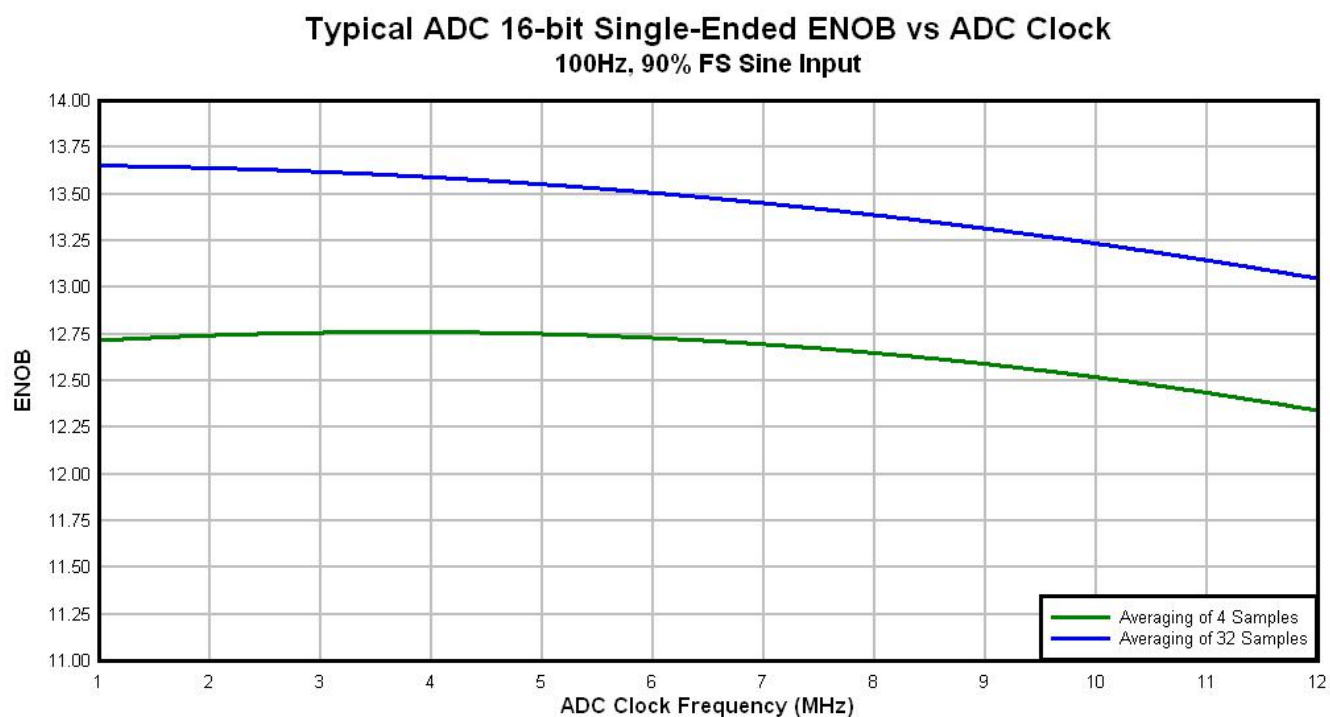


Figure 16. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

6.6.1.4 16-bit ADC with PGA characteristics with Chop enabled (ADC_PGA[PGACHPb] = 0)

Table 28. 16-bit ADC with PGA characteristics

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
I _{DDA_PGA}	Supply current	Low power (ADC_PGA[PGALPb]=0)	—	420	644	μA	2
I _{DC_PGA}	Input DC current		$\frac{2}{R_{PGAD}} \left(\frac{(V_{REFPGA} \times 0.583) - V_{CM}}{(Gain+1)} \right)$			A	3
		Gain =1, V _{REFPGA} =1.2V, V _{CM} =0.5V	—	1.54	—	μA	
		Gain =64, V _{REFPGA} =1.2V, V _{CM} =0.1V	—	0.57	—	μA	
G	Gain ⁴	• PGAG=0	0.95	1	1.05		R _{AS} < 100Ω
		• PGAG=1	1.9	2	2.1		
		• PGAG=2	3.8	4	4.2		
		• PGAG=3	7.6	8	8.4		
		• PGAG=4	15.2	16	16.6		
		• PGAG=5	30.0	31.6	33.2		
		• PGAG=6	58.8	63.3	67.8		
BW	Input signal bandwidth	• 16-bit modes	—	—	4	kHz	
		• < 16-bit modes	—	—	40	kHz	
PSRR	Power supply rejection ratio	Gain=1	—	-84	—	dB	V _{DDA} = 3V ±100mV, f _{VDDA} = 50Hz, 60Hz
CMRR	Common mode rejection ratio	• Gain=1	—	-84	—	dB	V _{CM} = 500mVpp, f _{VCM} = 50Hz, 100Hz
		• Gain=64	—	-85	—	dB	
V _{OFS}	Input offset voltage		—	0.2	—	mV	Output offset = V _{OFS} *(Gain+1)
T _{GSW}	Gain switching settling time		—	—	10	μs	5
dG/dT	Gain drift over full temperature range	• Gain=1	—	6	10	ppm/°C	
		• Gain=64	—	31	42	ppm/°C	
dG/dV _{DDA}	Gain drift over supply voltage	• Gain=1	—	0.07	0.21	%/V	V _{DDA} from 1.71 to 3.6V
		• Gain=64	—	0.14	0.31	%/V	

Table continues on the next page...

Peripheral operating requirements and behaviors

6. VDDA = 3.0V, reference select set for VDDA (DACx_CO:DACRFS = 1), high power mode(DACx_C0:LPEN = 0), DAC set to 0x800, Temp range from -40C to 105C

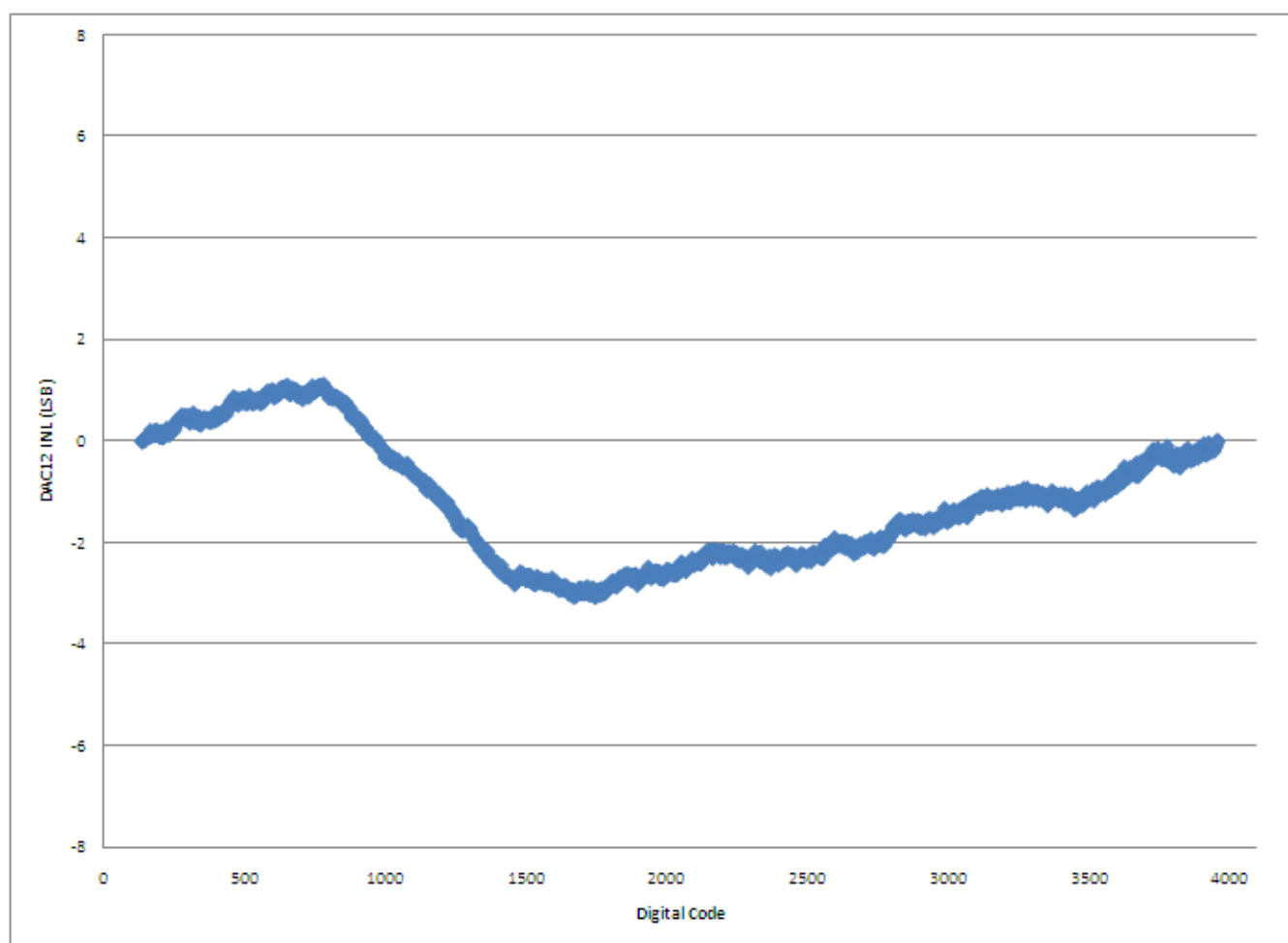


Figure 19. Typical INL error vs. digital code

Table 33. VREF full-range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim at nominal V_{DDA} and temperature=25C	1.1915	1.195	1.1977	V	
V_{out}	Voltage reference output — factory trim	1.1584	—	1.2376	V	
V_{out}	Voltage reference output — user trim	1.193	—	1.197	V	
V_{step}	Voltage reference trim step	—	0.5	—	mV	
V_{tdrift}	Temperature drift ($V_{max} - V_{min}$ across the full temperature range)	—	—	80	mV	
I_{bg}	Bandgap only current	—	—	80	μA	1
I_{lp}	Low-power buffer current	—	—	360	μA	1
I_{hp}	High-power buffer current	—	—	1	mA	1
ΔV_{LOAD}	Load regulation • current = ± 1.0 mA	—	200	—	μV	1, 2
T_{stup}	Buffer startup time	—	—	20	μs	
V_{vdrift}	Voltage drift ($V_{max} - V_{min}$ across the full voltage range)	—	2	—	mV	1

1. See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.
2. Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

Table 34. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_A	Temperature	0	50	$^{\circ}C$	

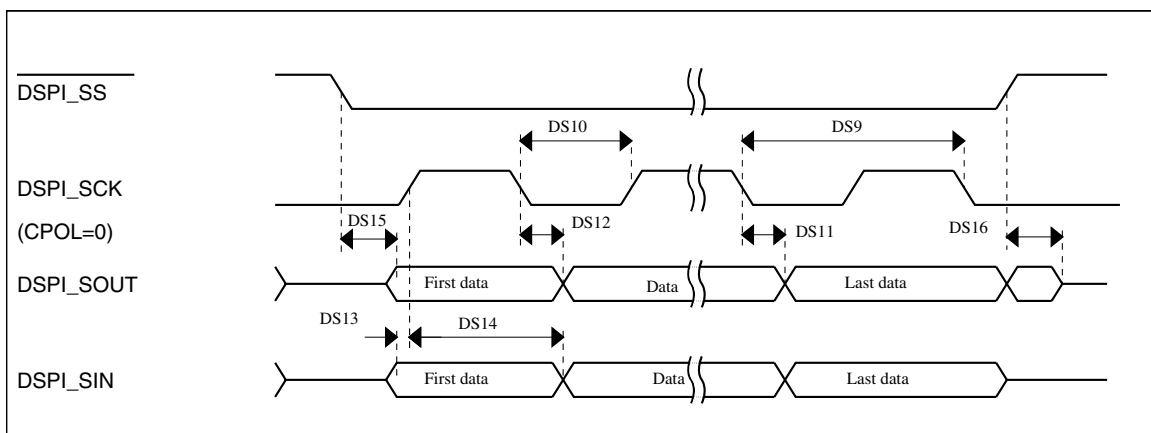
Table 35. VREF limited-range operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim	1.173	1.225	V	

Symbol	Description	Min	Max	Unit	Notes
VREFH	Voltage reference output with factory trim	1.173	1.225	V	
VREFL	Voltage reference output	0.38	0.42	V	
IBIASP_AFE_4 μA	P-bias current output	3.5 μ	4.5 μ	A	

Table 40. Slave mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
	Frequency of operation	—	6.25	MHz
DS9	DSPI_SCK input cycle time	$8 \times t_{\text{BUS}}$	—	ns
DS10	DSPI_SCK input high/low time	$(t_{\text{SCK}}/2) - 4$	$(t_{\text{SCK}}/2) + 4$	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	20	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SS to DSPI_SCK input setup	2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI_SS}}$ active to DSPI_SOUT driven	—	19	ns
DS16	$\overline{\text{DSPI_SS}}$ inactive to DSPI_SOUT not driven	—	19	ns

**Figure 24. DSPI classic SPI timing — slave mode**

6.8.4 I²C switching specifications

See [General switching specifications](#).

6.8.5 UART switching specifications

See [General switching specifications](#).

6.8.6 I2S/SAI Switching Specifications

This section provides the AC timing for the I2S/SAI module in master mode (clocks are driven) and slave mode (clocks are input). All timing is given for noninverted serial clock polarity (TCR2[BCP] is 0, RCR2[BCP] is 0) and a noninverted frame sync (TCR4[FSP] is 0, RCR4[FSP] is 0). If the polarity of the clock and/or the frame sync have been inverted, all the timing remains valid by inverting the bit clock signal (BCLK) and/or the frame sync (FS) signal shown in the following figures.

6.8.6.1 Normal Run, Wait and Stop mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in Normal Run, Wait and Stop modes.

Table 41. I2S/SAI master mode timing in Normal Run, Wait and Stop modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	-1.0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	20.5	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

Pinout

81 MAP BGA	80 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
L3	21	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18								
K5	22	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23								
L7	—	RTC_ WAKEUP_B	RTC_ WAKEUP_B	RTC_ WAKEUP_B								
L4	23	XTAL32	XTAL32	XTAL32								
L5	24	EXTAL32	EXTAL32	EXTAL32								
K6	25	VBAT	VBAT	VBAT								
J6	26	PTA0	JTAG_TCLK/ SWD_CLK/ EZP_CLK	TSIO_CH1	PTA0	UART0_CTS_ b/ UART0_COL_ b	FTM0_CH5				JTAG_TCLK/ SWD_CLK	EZP_CLK
H8	27	PTA1	JTAG_TDI/ EZP_DI	TSIO_CH2	PTA1	UART0_RX	FTM0_CH6				JTAG_TDI	EZP_DI
J7	28	PTA2	JTAG_TDO/ TRACE_SWO/ EZP_DO	TSIO_CH3	PTA2	UART0_TX	FTM0_CH7				JTAG_TDO/ TRACE_SWO	EZP_DO
H9	29	PTA3	JTAG_TMS/ SWD_DIO	TSIO_CH4	PTA3	UART0_RTS_ b	FTM0_CH0				JTAG_TMS/ SWD_DIO	
J8	30	PTA4/ LLWU_P3	NMI_b/ EZP_CS_b	TSIO_CH5	PTA4/ LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
K7	31	PTA5	DISABLED		PTA5		FTM0_CH2		CMP2_OUT	I2S0_TX_ BCLK	JTAG_TRST_ b	
E5	—	VDD	VDD	VDD								
G3	—	VSS	VSS	VSS								
K8	32	PTA12	CMP2_IN0	CMP2_IN0	PTA12	CAN0_TX	FTM1_CH0			I2S0_TXD0	FTM1_QD_ PHA	
L8	33	PTA13/ LLWU_P4	CMP2_IN1	CMP2_IN1	PTA13/ LLWU_P4	CAN0_RX	FTM1_CH1			I2S0_TX_FS	FTM1_QD_ PHB	
K9	34	PTA14	DISABLED		PTA14	SPI0_PCS0	UART0_TX			I2S0_RX_ BCLK	I2S0_TXD1	
L9	35	PTA15	DISABLED		PTA15	SPI0_SCK	UART0_RX			I2S0_RXD0		
J10	36	PTA16	DISABLED		PTA16	SPI0_SOUT	UART0_CTS_ b/ UART0_COL_ b			I2S0_RX_FS	I2S0_RXD1	
H10	37	PTA17	ADC1_SE17	ADC1_SE17	PTA17	SPI0_SIN	UART0_RTS_ b			I2S0_MCLK		
L10	38	VDD	VDD	VDD								
K10	39	VSS	VSS	VSS								
L11	40	PTA18	EXTAL0	EXTAL0	PTA18		FTM0_FLT2	FTM_CLKIN0				
K11	41	PTA19	XTAL0	XTAL0	PTA19		FTM1_FLT0	FTM_CLKIN1		LPTMR0_ ALT1		

81 MAP BGA	80 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
J9	—	NC	NC	NC								
J4	—	NC	NC	NC								
H11	—	NC	NC	NC								
F11	—	NC	NC	NC								
E11	—	NC	NC	NC								
D11	—	NC	NC	NC								
E10	—	NC	NC	NC								
F10	—	NC	NC	NC								
F9	—	NC	NC	NC								
F8	—	NC	NC	NC								
E8	—	NC	NC	NC								
B6	—	NC	NC	NC								
A6	—	NC	NC	NC								
A5	—	NC	NC	NC								
B5	—	NC	NC	NC								
B4	—	NC	NC	NC								
A4	—	NC	NC	NC								
A10	—	NC	NC	NC								
A9	—	NC	NC	NC								
B1	—	NC	NC	NC								
C2	—	NC	NC	NC								
C1	—	NC	NC	NC								
D2	—	NC	NC	NC								
D1	—	NC	NC	NC								
E1	—	NC	NC	NC								

8.2 K10 Pinouts

The below figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

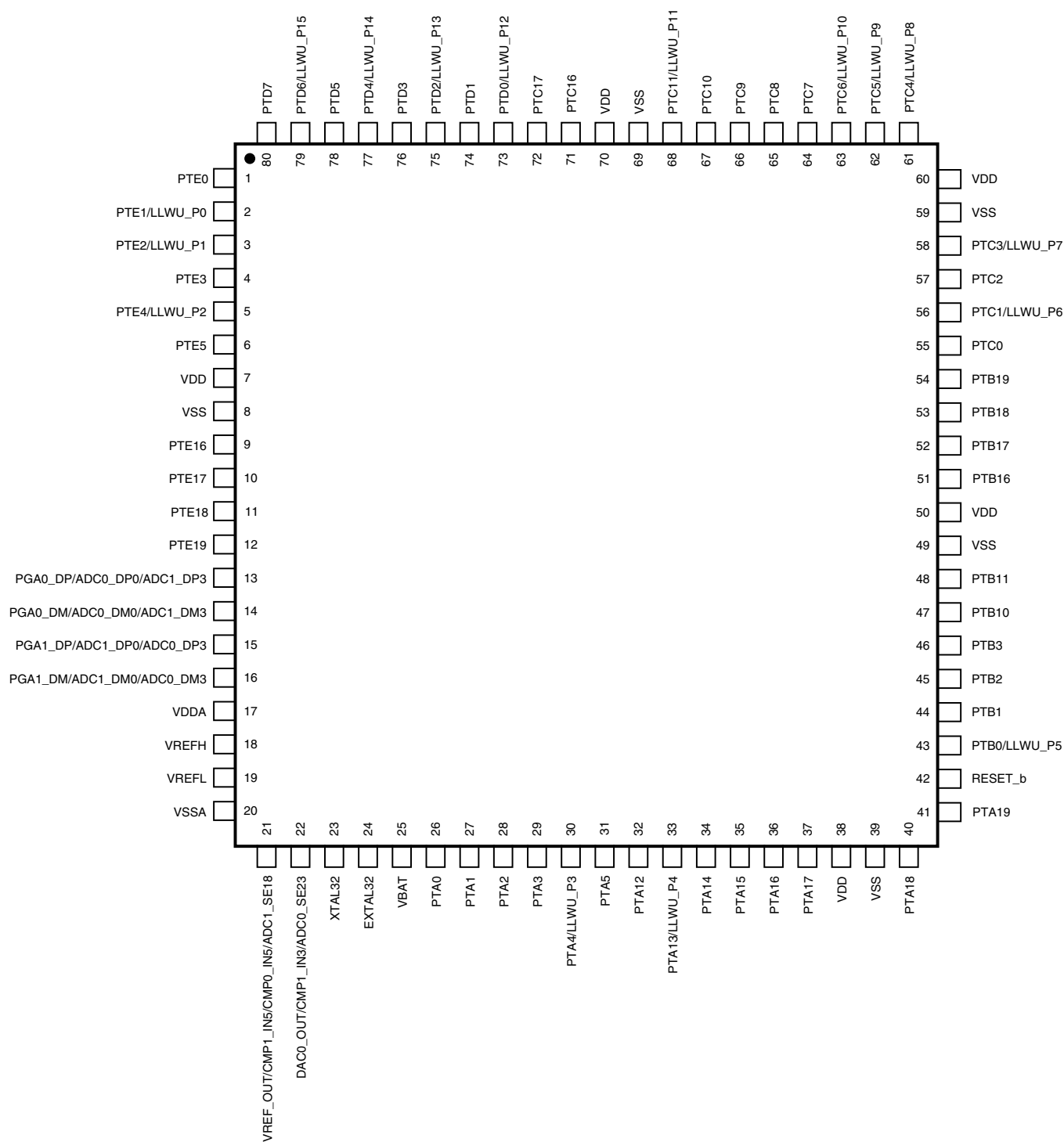


Figure 29. K10 80 LQFP Pinout Diagram